

In the Claims:

Please cancel claims 2 and 4 without prejudice or disclaimer.

Please amend claims 1 and 6, as follows:

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B1  
Claim 1 (currently amended) A slurry used in a chemical mechanical polishing (CMP) process on a ruthenium thin film or a ruthenium alloy thin film, the slurry comprising:

an oxidant consisting essentially of ceric ammonium nitrate  $[(\text{NH}_4)_2\text{Ce}(\text{NO}_3)_6]$

an abrasive consisting essentially of inorganic particles, and

an acid selected from the group consisting of  $\text{HNO}_3$ ,  $\text{H}_2\text{SO}_4$ ,  $\text{HCl}$ ,  $\text{H}_3\text{PO}_4$ , and mixtures thereof.

Claim 2 (currently canceled)

Claim 3 (previously amended) The slurry according to claim 1, wherein the ceric ammonium nitrate is present in an amount ranging from about 1 to about 10% by weight of the slurry.

Claim 4 (currently canceled)

Claim 5 (original) The slurry according to claim 2, wherein the acid is  $\text{HNO}_3$  and is present in an amount ranging from about 1 to about 10% by weight of the slurry.

Claim 6 (currently amended) The slurry according to claim 2 1, wherein the inorganic particles of the abrasive are selected from the group consisting of  $\text{CeO}_2$  particles,  $\text{ZrO}_2$  particles,  $\text{Al}_2\text{O}_3$  particles and mixtures thereof.

Claim 7 (previously amended) The slurry according to claim 1, wherein a grain size of the abrasive is less than 1  $\mu\text{m}$ .

Claim 8 (previously mended) The slurry according to claim 1, wherein the abrasive is used in an amount ranging from about 1 to about 5% by weight of the slurry.

Claim 9 (original) The slurry according to claim 2, wherein a pH of the composition ranges from about 1 to about 7.

Claim 10 (original) The slurry according to claim 2, wherein the pH of the composition ranges from about 1 to about 3.

Claim 11 (original) The slurry according to claim 2, further comprising a buffer.

Claim 12 (original) The slurry according to claim 11, wherein the buffer comprises a mixed solution of approximately equal molar amounts of an organic acid and an organic acid salt.

Claim 13 (original) The slurry according to claim 12, wherein the buffer comprises a mixed solution of acetic acid and acetic acid salt.

Claims 14-23 (previously canceled)

Please add new claim 24, as follows:

Claim 24 (new) A slurry used in a chemical mechanical polishing (CMP) process on a ruthenium thin film or a ruthenium alloy thin film, the slurry comprising:  
a single oxidant consisting essentially of ceric ammonium nitrate  
 $[(\text{NH}_4)_2\text{Ce}(\text{NO}_3)_6]$   
an abrasive consisting essentially of inorganic particles.